

Tomohiro Yamaguchi

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/741051/publications.pdf>

Version: 2024-02-01

31
papers

887
citations

1307594

7
h-index

713466

21
g-index

31
all docs

31
docs citations

31
times ranked

1039
citing authors

#	ARTICLE	IF	CITATIONS
1	RF-Molecular Beam Epitaxy Growth and Properties of InN and Related Alloys. Japanese Journal of Applied Physics, 2003, 42, 2549-2559.	1.5	394
2	Valence band ordering in $\hat{\text{I}}^2\text{-Ga}_{2\text{O}_3}$ studied by polarized transmittance and reflectance spectroscopy. Japanese Journal of Applied Physics, 2015, 54, 112601.	1.5	261
3	Indium Droplet Elimination by Radical Beam Irradiation for Reproducible and High-Quality Growth of InN by RF Molecular Beam Epitaxy. Applied Physics Express, 0, 2, 051001.	2.4	68
4	Spectroscopic ellipsometry studies on $\hat{\text{I}}^2\text{-Ga}_{2\text{O}_3}$ films and single crystal. Japanese Journal of Applied Physics, 2016, 55, 1202B2.	1.5	33
5	Growth of rocksalt-structured $\text{Mg}_x\text{Zn}_{1-x}\text{O}$ ($x \geq 0.5$) films on MgO substrates and their deep-ultraviolet luminescence. Applied Physics Express, 2016, 9, 111102.	2.4	26
6	Systematic investigation of surface and bulk electronic structure of undoped In-polar InN epilayers by hard X-ray photoelectron spectroscopy. Journal of Applied Physics, 2013, 114, .	2.5	17
7	Structural evaluation of ions-implanted GaN films by photothermal deflection spectroscopy. AIP Advances, 2018, 8, .	1.3	15
8	Relation Between Electrical and Optical Properties of $\text{p}^+\text{-Type NiO}$ Films. Physica Status Solidi (B): Basic Research, 2018, 255, 1700311.	1.5	13
9	Nitride-MBE system for in situ synchrotron X-ray measurements. Japanese Journal of Applied Physics, 2016, 55, 05FB05.	1.5	8
10	Identification of free and bound exciton emission of MgO single crystal in vacuum ultraviolet spectral range. Applied Physics Letters, 2021, 119, .	3.3	7
11	Electron-beam incident-angle-resolved cathodoluminescence studies on bulk ZnO crystals. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 869-872.	0.8	6
12	Impact of hydrochloric acid on the epitaxial growth of In_{2O_3} films on (0001)- Al_{2O_3} substrates by mist CVD. Applied Physics Express, 2020, 13, 075504.	2.4	6
13	Surface and bulk electronic structures of heavily Mg-doped InN epilayer by hard X-ray photoelectron spectroscopy. Journal of Applied Physics, 2017, 121, .	2.5	5
14	In Situ Synchrotron X-ray Diffraction Reciprocal Space Mapping Measurements in the RF-MBE Growth of GaInN on GaN and InN. Crystals, 2019, 9, 631.	2.2	5
15	MOCVD Growth and Investigation of InGaN/GaN Heterostructure Grown on AlGaIn/GaN-on-Si Template. Applied Sciences (Switzerland), 2019, 9, 1746.	2.5	4
16	Photoelectron spectroscopic study on electronic state of corundum In_2O_3 epitaxial thin film grown by mist-CVD. Japanese Journal of Applied Physics, 2020, 59, SIIG12.	1.5	4
17	Effect of thermal annealing on photoexcited carriers in nitrogen-ion-implanted $\hat{\text{I}}^2\text{-Ga}_2\text{O}_3$ crystals detected by photocurrent measurement. AIP Advances, 2021, 11, .	1.3	3
18	Mist Chemical Vapor Deposition Growth of $\hat{\text{I}}^2\text{O}_3$ Films Using Indium Oxide Powder as Source Precursor. Physica Status Solidi (B): Basic Research, 0, , 2100414.	1.5	3

#	ARTICLE	IF	CITATIONS
19	Fabrication of a-plane InN nanostructures on patterned a-plane GaN template by ECR-MBE. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2012, 209, 447-450.	1.8	2
20	Effect of (GaN/AlN) alternating source feeding buffer layer in GaN growth on Al ₂ O ₃ and silicon by RF-MBE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013, 10, 1549-1552.	0.8	2
21	Fabrication of Ag dispersed ZnO films by molecular precursor method and application in GaInN blue LED. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017, 214, 1600598.	1.8	1
22	Surface and bulk electronic structures of unintentionally and Mg-doped In _{0.7} Ga _{0.3} N epilayer by hard X-ray photoelectron spectroscopy. <i>Journal of Applied Physics</i> , 2018, 123, 095701.	2.5	1
23	Epitaxial mist chemical vapor deposition growth and characterization of Cu ₃ N films on (0001)±-Al ₂ O ₃ substrates. <i>Applied Physics Express</i> , 2020, 13, 075505.	2.4	1
24	Plasma excited molecular beam epitaxy proposal and achievements through R&D of compound semiconductor materials and devices. <i>Japanese Journal of Applied Physics</i> , 0, , .	1.5	1
25	VUV emission properties of rock salt structured MgZnO microcrystals prepared on quartz glass substrates. <i>Physica Status Solidi (B): Basic Research</i> , 0, , 2100354.	1.5	1
26	The strain-controlled GaN growth on Si by RF-MBE. , 2012, , .		0
27	GaN growth on (111)Al substrates by CS-MBE and their chemical lift-off technique. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013, 10, 385-387.	0.8	0
28	Optical properties of Ga _{0.82} In _{0.18} N homojunction blue-green light-emitting-diode grown by radio-frequency plasma-assisted molecular beam epitaxy. <i>Transactions of the Materials Research Society of Japan</i> , 2015, 40, 149-152.	0.2	0
29	Surface plasmon resonant emission from Ag dispersed ZnO films fabricated by molecular precursor method. , 2016, , .		0
30	Observation of Electroreflectance Spectra of η -Ga ₂ O ₃ Single Crystal. , 2019, , .		0
31	Selective observation of transverse optical phonons of Au modes to evaluate free charge carrier parameters in η -Ga ₂ O ₃ substrate and homoepitaxial film. <i>Applied Physics Letters</i> , 2021, 118, 252101.	3.3	0